

Amendments to the Specification:

Please replace the section entitled "Related Applications" after the title and before the "Field of the Invention" with the following amended "Related Applications" section:

--The present application is a continuation-in-part of United States Patent Application Serial No. 09/968,391 entitled "METHOD OF N₂O GROWTH OF AN OXIDE LAYER ON A SILICON CARBIDE LAYER" filed October 1, 2001 (~~Attorney Docket No. 5308-157IP~~) which claims priority from United States Provisional Application Serial No. 60/294,307 entitled "METHOD OF N₂O GROWTH OF AN OXIDE LAYER ON A SILICON CARBIDE LAYER" filed May 30, 2001 and claims priority from, and is a continuation-in-part of, United States Patent Application Serial No. 09/834,283, now United States Patent No. 6,610,366, filed April 12, 2001 entitled "METHOD OF N₂O ANNEALING AN OXIDE LAYER ON A SILICON CARBIDE LAYER" which claims priority from United States Provisional Application Serial No. 60/237,822, entitled "METHOD OF IMPROVING AN INTERFACE BETWEEN A SILICON CARBIDE LAYER AND AN OXIDE LAYER" and United States Provisional Application Serial No. 60/237,426 entitled "SIC POWER MOSFET AND METHOD OF FABRICATION" which were filed October 3, 2000. The disclosures of each of the above-cited applications are incorporated herein by reference as if set forth fully herein.--